

1 **ABSTRACT OF THE DISCLOSURE**

2 The invention encompasses a method of incorporating nitrogen into
3 a silicon-oxide-containing layer. The silicon-oxide-containing layer is
4 exposed to a nitrogen-containing plasma to introduce nitrogen into the
5 layer. The nitrogen is subsequently thermally annealed within the layer
6 to bond at least some of the nitrogen to silicon within the layer. The
7 invention also encompasses a method of forming a transistor. A gate
8 oxide layer is formed over a semiconductive substrate. The gate oxide
9 layer comprises silicon dioxide. The gate oxide layer is exposed to a
10 nitrogen-containing plasma to introduce nitrogen into the layer, and the
11 layer is maintained at less than or equal to 400°C during the exposing.
12 Subsequently, the nitrogen within the layer is thermally annealed to bond
13 at least a majority of the nitrogen to silicon. At least one conductive
14 layer is formed over the gate oxide layer. Source/drain regions are
15 formed within the semiconductive substrate, and are gatedly connected
16 to one another by the at least one conductive layer. The invention also
17 encompasses transistor structures.

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